NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1425** is Designed for Class AB Linear Base Station Applications in the 800-900 MHz Frequency Range.

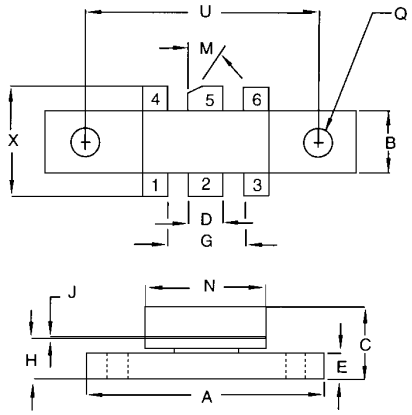
FEATURES INCLUDE:

- Gold Metalization
- Input Matching
- Common Emitter
- Emitter Ballast Resistors

MAXIMUM RATINGS

I_C	5.0 A
V_{CBO}	50 V
V_{CES}	45 V
P_{DISS}	43 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	3.0 ^{O}C/W

PACKAGE STYLE .230 6L FLG



	Millimeters		Inches	
Dim	Min	Max	Min	Max
A	24.64	24.89	0.970	0.980
B	5.72	5.96	0.225	0.235
C	6.10	6.60	0.240	0.260
D	2.93	3.17	0.115	0.125
E	2.72	2.97	0.107	0.117
G	4.33	5.33	0.190	0.210
H	4.07	4.57	0.160	0.180
J	0.11	0.15	0.004	0.006
K	10.30	11.43	0.425	0.450
M	45 NOM		45 NOM	
N	9.02	9.77	0.355	0.385
Q	3.05	3.30	0.120	0.130
U	18.29	18.54	0.720	0.730

1,3,4,6 = EMITTER 2 = BASE
5 = COLLECTOR

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 100 mA	50			V
BV_{CEO}	I_C = 40 mA	25			V
BV_{CER}	I_C = 50 mA R_{BE} = 22 Ω	50			V
BV_{EBO}	I_E = 10 mA	3.5			V
I_{CBO}	V_{CB} = 24 V			2.0	mA
h_{FE}	V_{CE} = 10 V I_C = 200 mA	20		100	---
C_{ob}	V_{CB} = 24 V f = 1.0 MHz		40	50	pF
P_{out}	V_{CC} = 24 V P_{in} = 5.3 W f = 960 MHz	30			W
G_P		7.5			dB
η_C		45	50		%

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Specifications are subject to change without notice.

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